

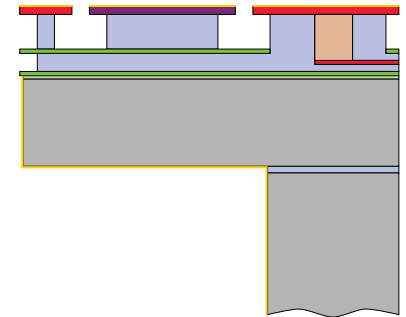
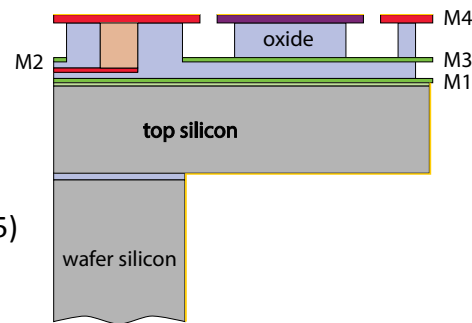
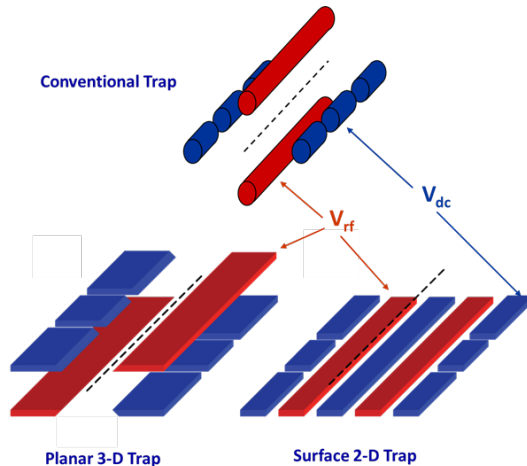
Surface Electrode – Triangle – Ion Trap Technology Overview

Matthew Blain
Daniel Stick

6 August 2013
NIST Boulder

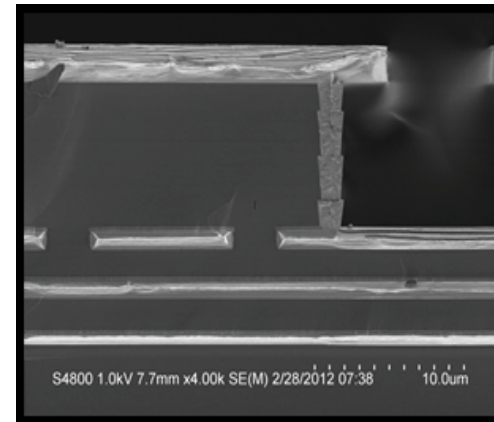
Surface Electrode Ion Trap Fabrication

4-metal-layer process modified from Sandia 0.35 μm Al/SiO₂ CMOS Process



J. Chiaverini, *et al.*, Quant. Inf. Comp. 5, 419 (2005)

- 1.2/2.5 μm Al 4LM technology
- Trap flow: ~300 ops, 11 mask levels used 17x
- Interposer flow: ~320 ops, 15 mask levels used 21x
- 10 μm oxide separating RF(M4), ground (M3)
- Precision Chip thru-holes
- Release singulation
- Precisely recessed oxide
- Routing on M2
- Gold coating from front and back side





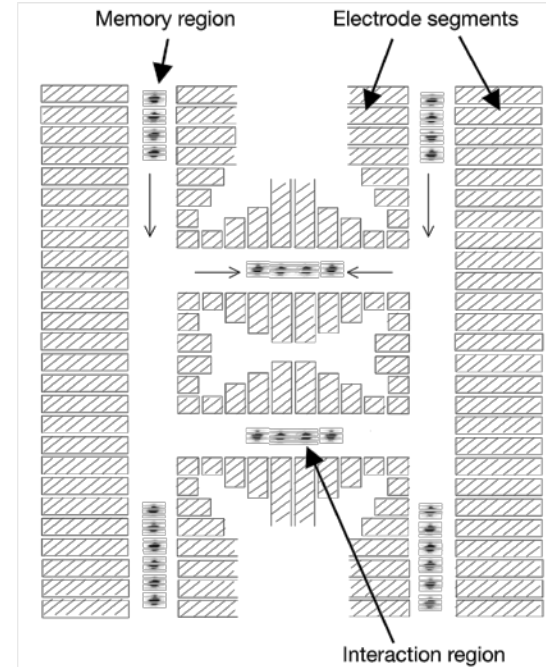
Possible geometries

multi-layer technology advantages

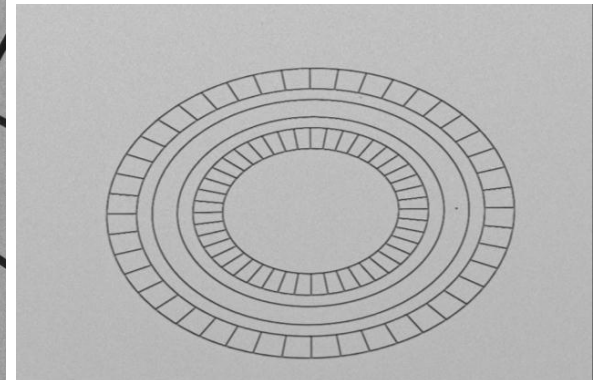
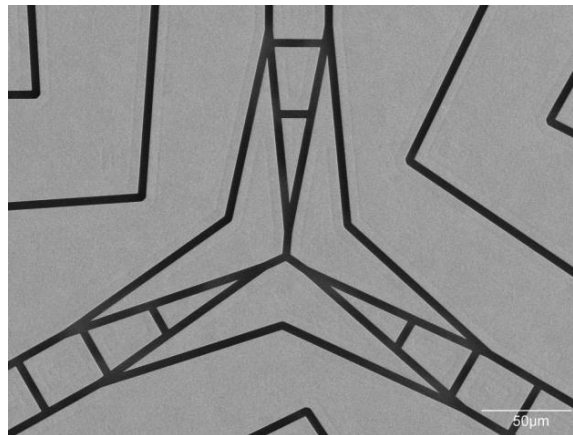
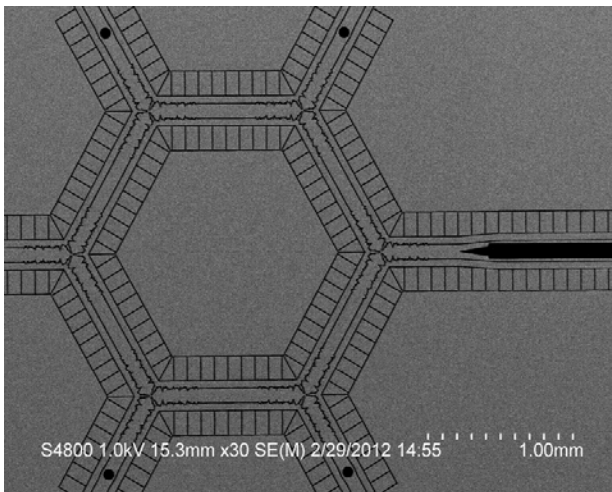
4-level-metal devices allow for:

- No exposed routing
- Islanded electrodes
- New topologies
- 5th layer for μ -wave delivery

Imagine your trap geometry:
it can be realized



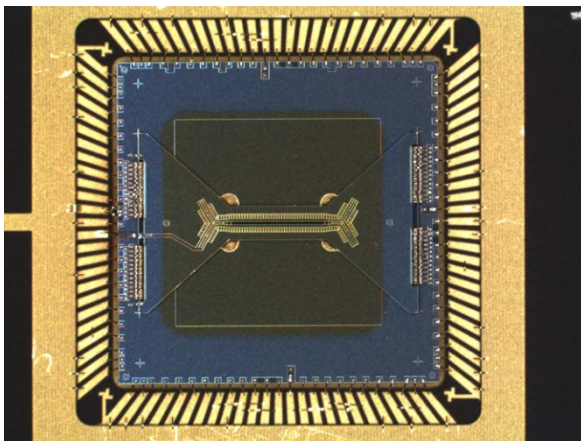
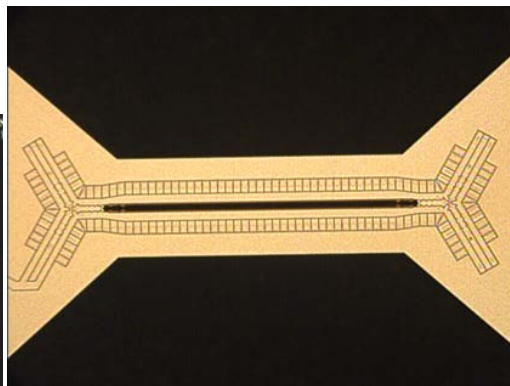
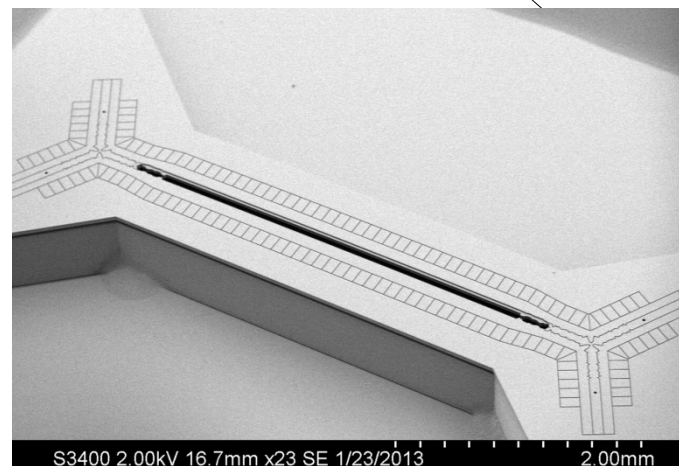
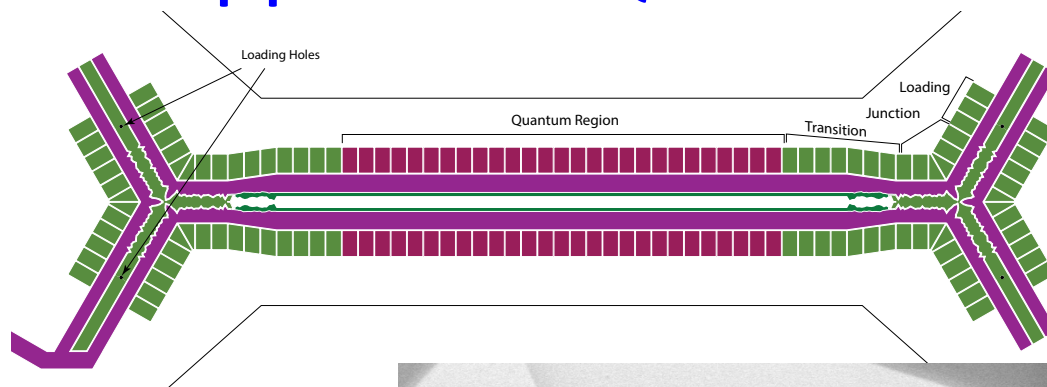
D. Kielpinski, *et al.* Nature 417, 209 (2002).



HOA trap platform *high optical access trap*

Optimized surface electrode trap platform for QIP

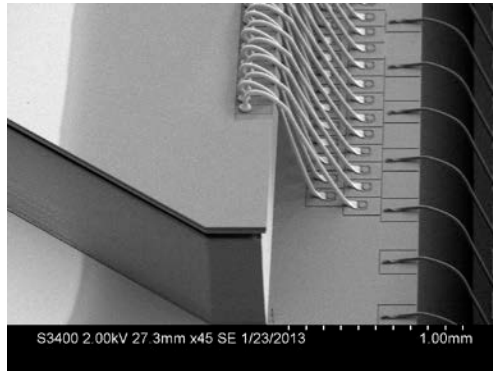
- Release singulation
- Unique shape
- Greatly improved optical access:
 - Larger trap depth
 - Higher trap frequencies
 - Less optical scatter



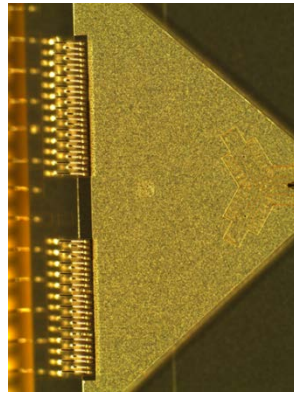


Interposers for Surface Traps

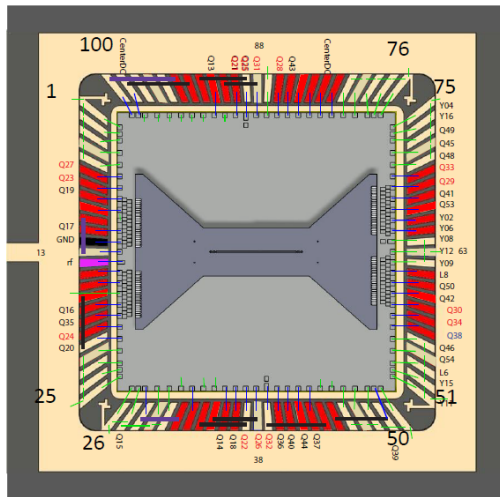
- Chip-to-interposer wires give unobstructed laser access to trapping region
- Redistribution layer (RDL) routes trap I/O (2-sides) to package (4-sides)



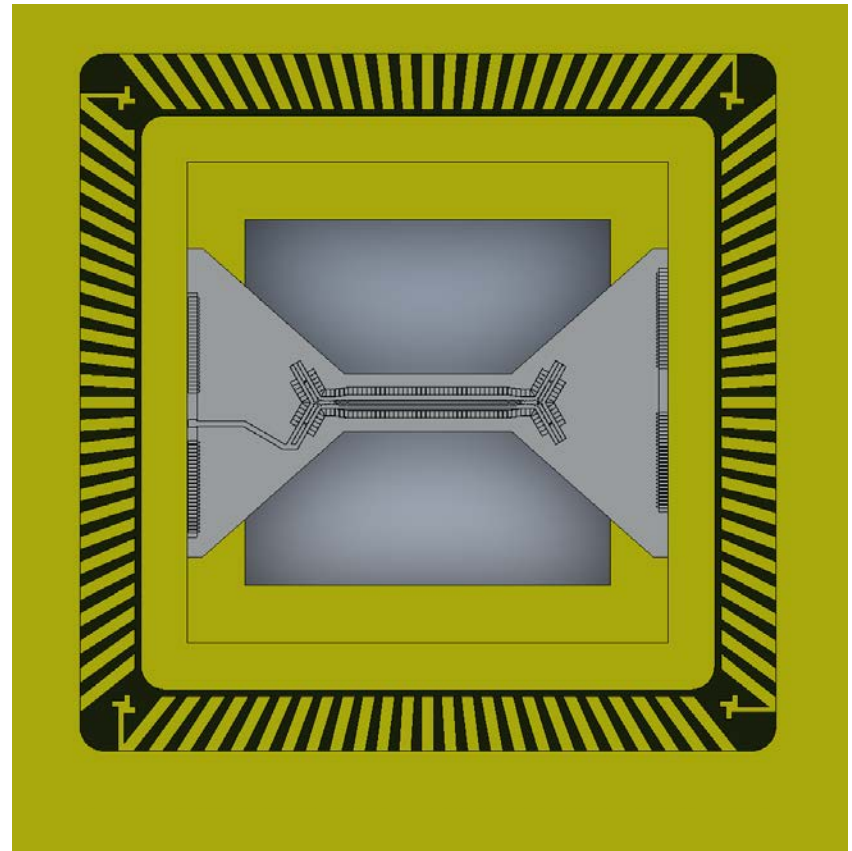
Sandia 48-pin chambers



Version 5



■ rf gnd ■ rf ■ Control ■ GND ■ Not used. The trap may short these pins to ground or to control pins.

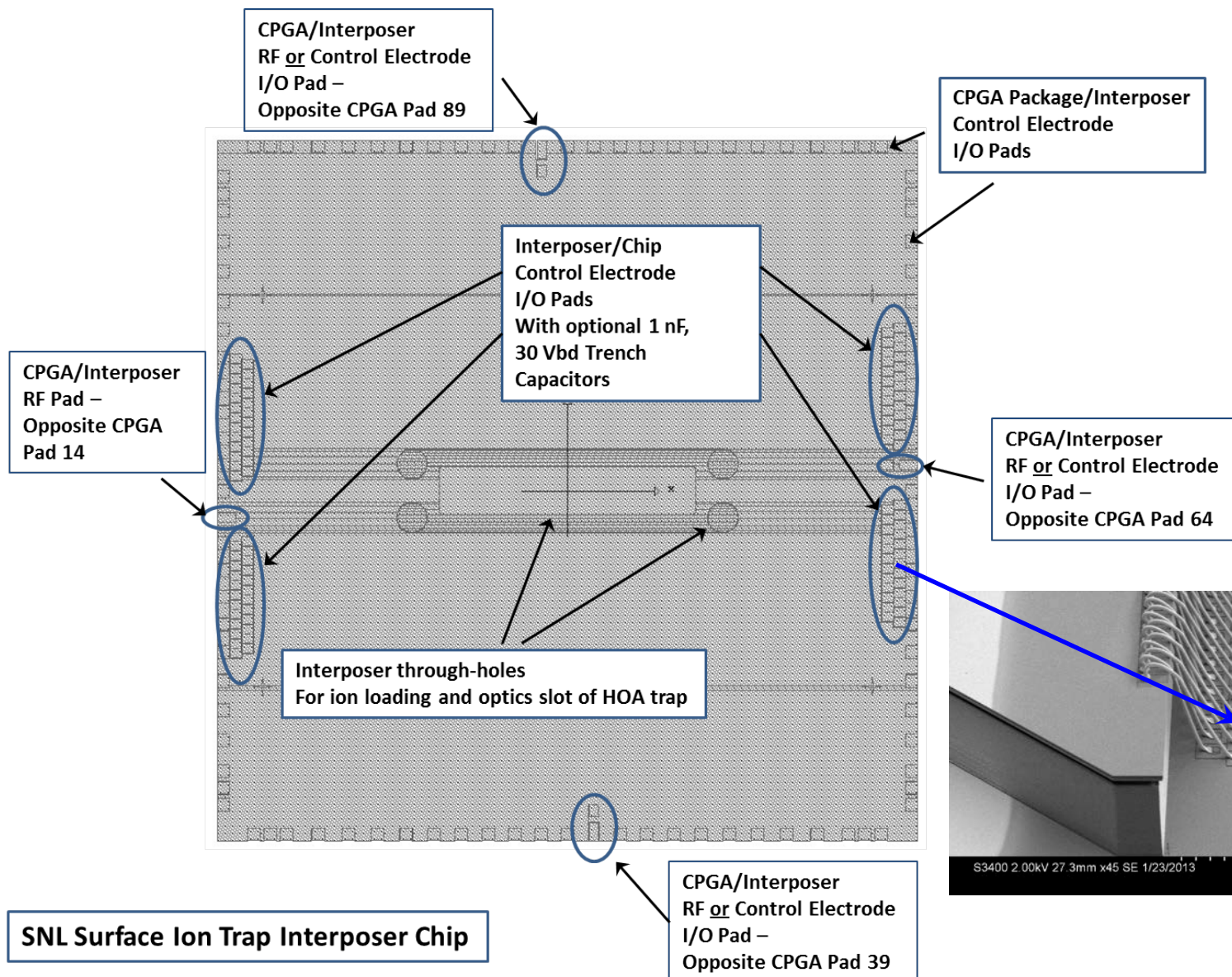


- Interposer can support:
 - Passive and active electronics
 - Future and (some) existing traps

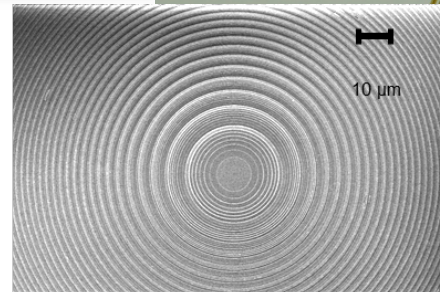
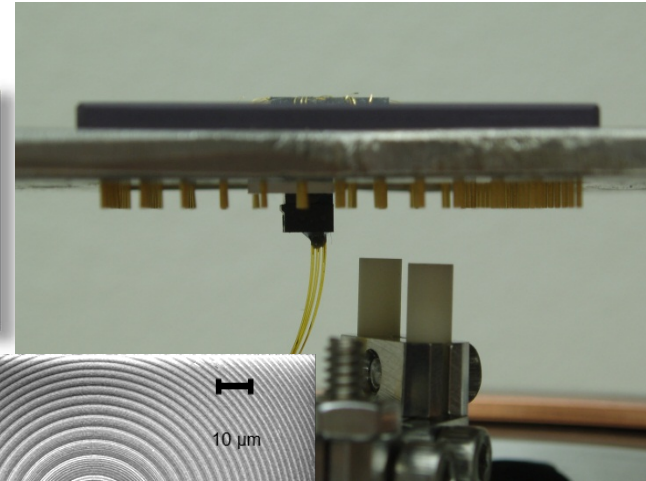
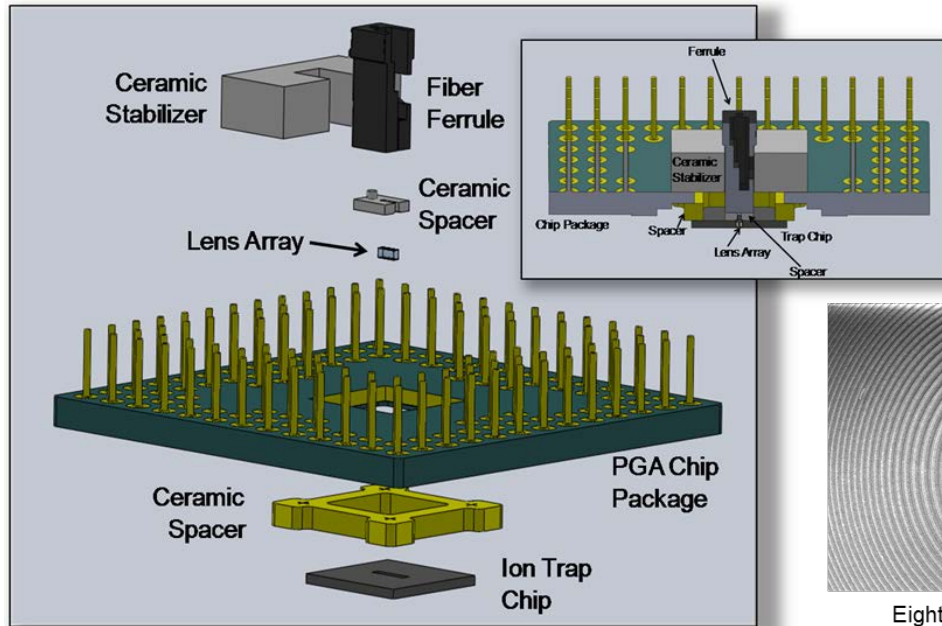


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Interposers for Surface Traps

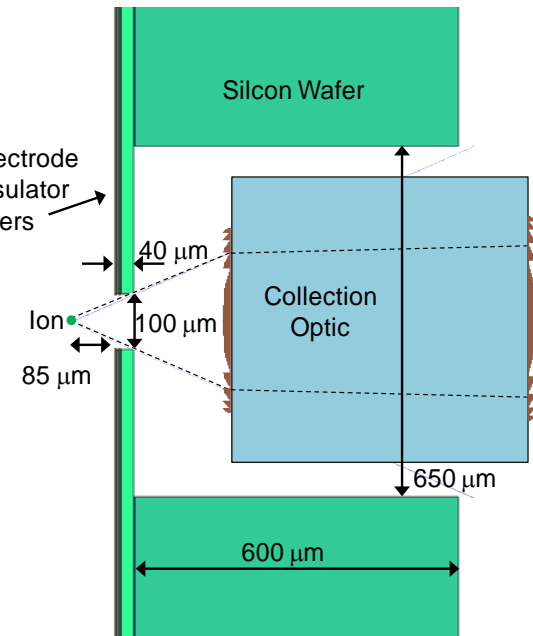


Integrated Optics



Eight level F/1 fused silica DOE

Trap Electrode and Insulator Layers



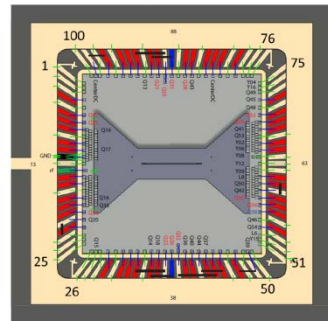
- Optics have been integrated into linear surface ion trap.
- No detrimental effects to ultra-high vacuum.
- Successful shuttling with same voltage solutions as linear trap without integrated optics.
- Compensated any charging on dielectric lenses.
- Dielectric lenses ~150 microns away from ion.

G. R. Brady, *et al.* Appl. Phys. B: Lasers and Optics 103, 801-808 (2011).

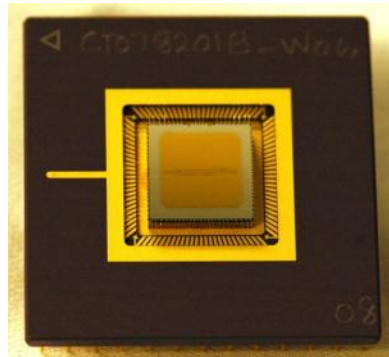
Packaging and testing

Plug-and-trap design

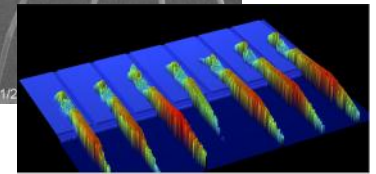
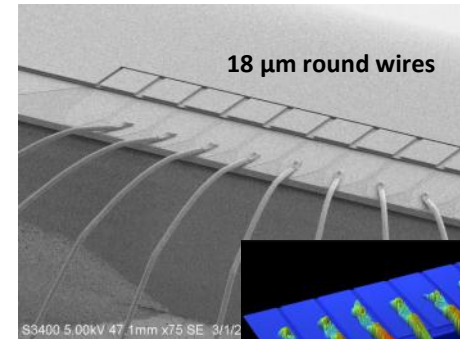
MQCO 48 pin chambers



Version 7 in terposer with capacitors 70-76 shorted



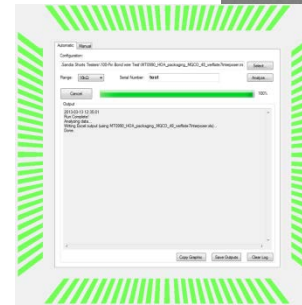
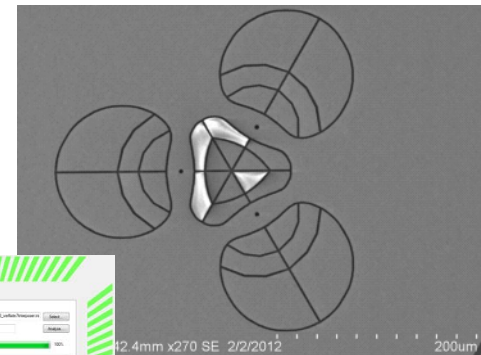
Low profile wirebonding



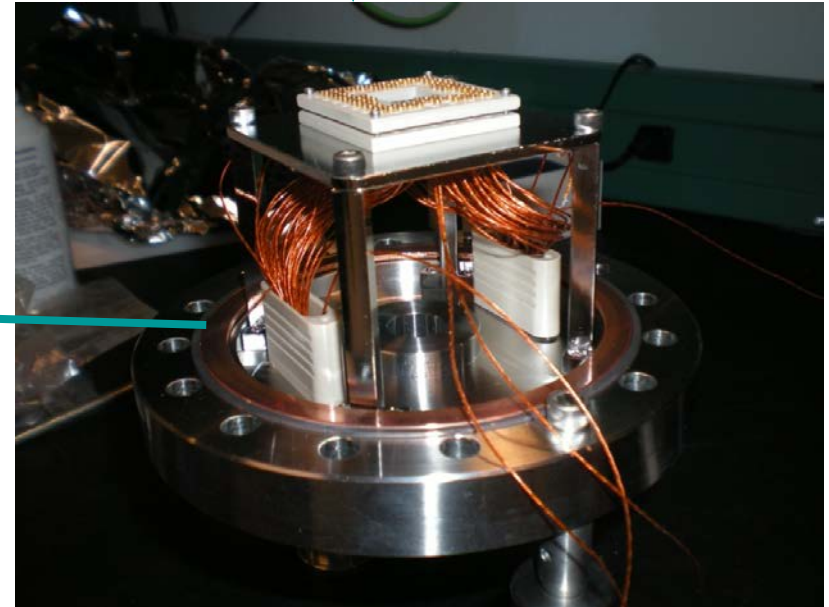
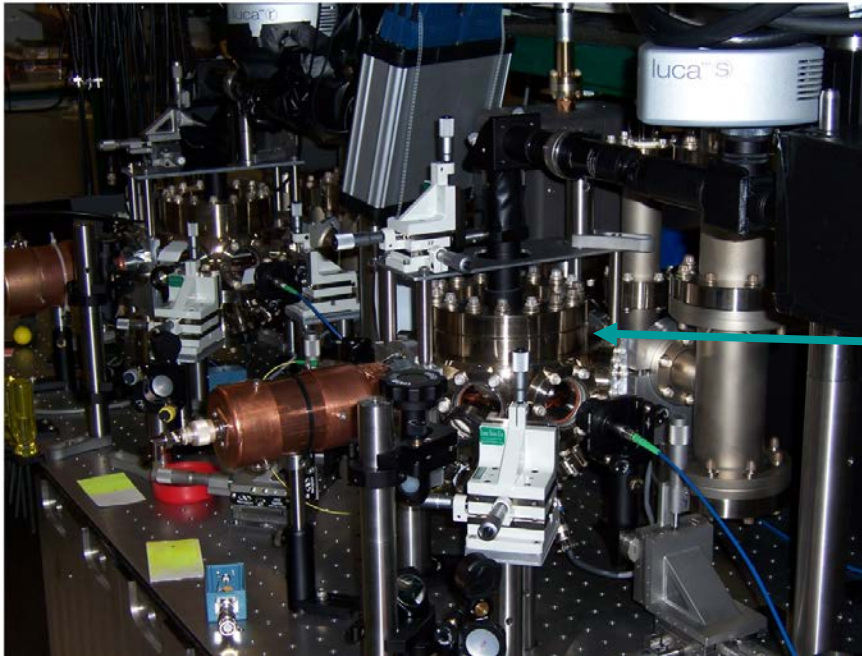
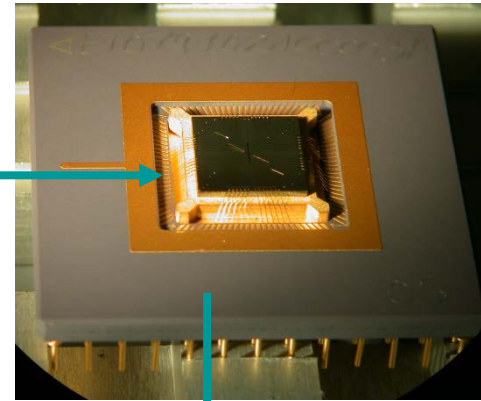
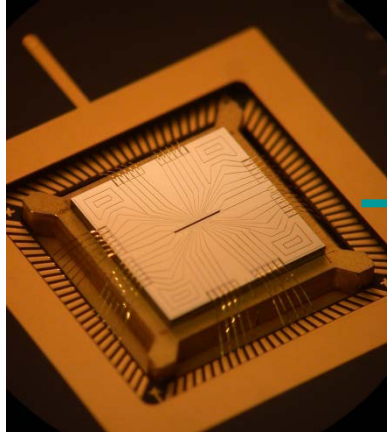
Plug-and-trap design

- Standard package part for chip ion traps
- Most trapping groups can accommodate the package
- Low profile wirebonds: good optical access
- Checks for opens and shorts > 40 MΩ

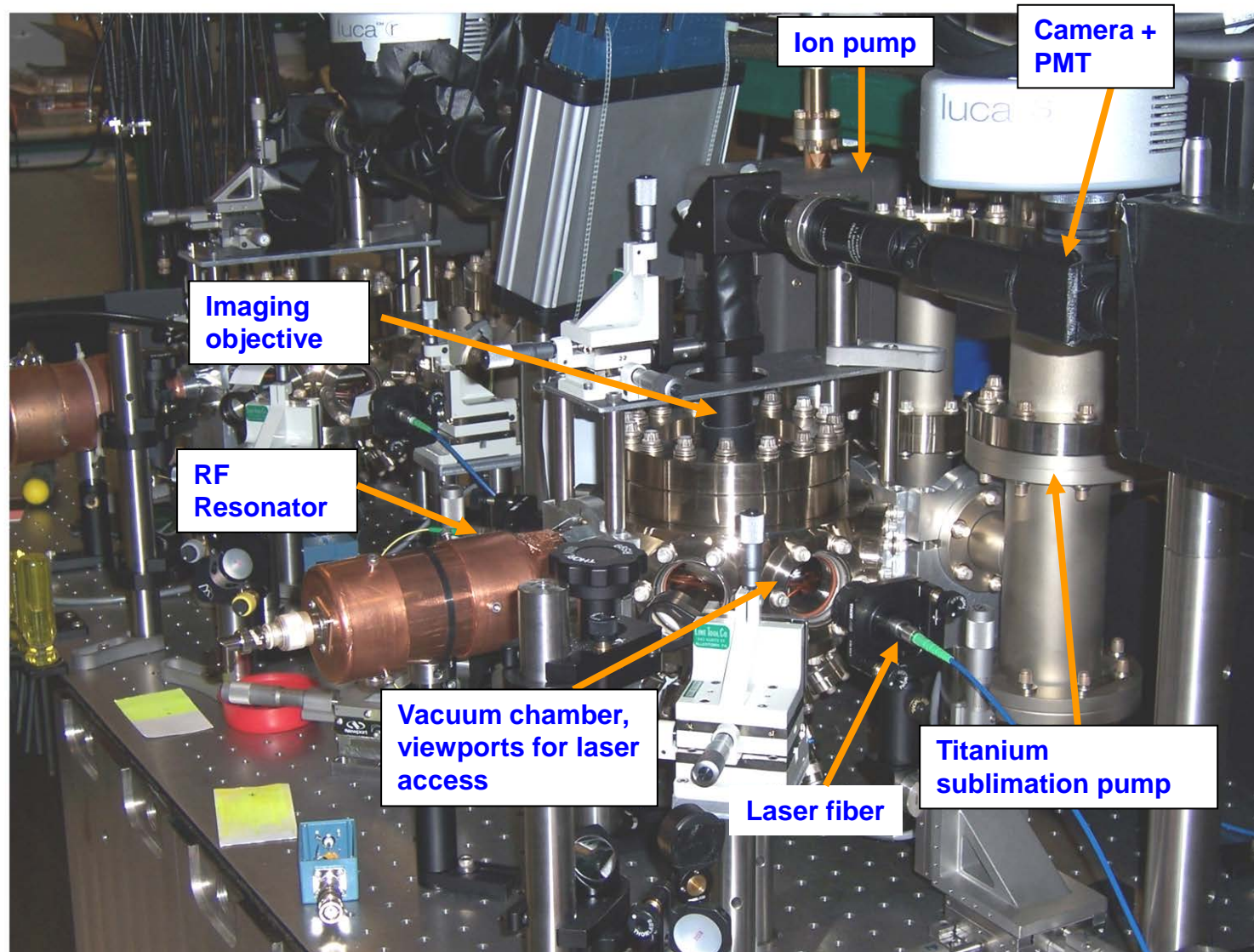
Parametric verification



Trap operational testing

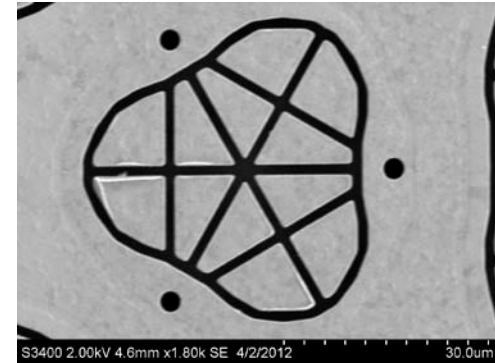
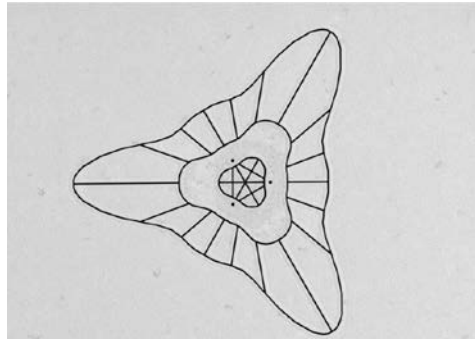
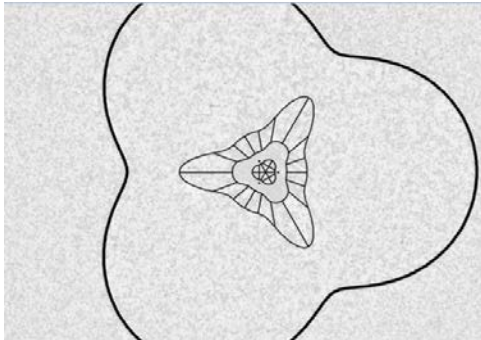


Trap operational testing

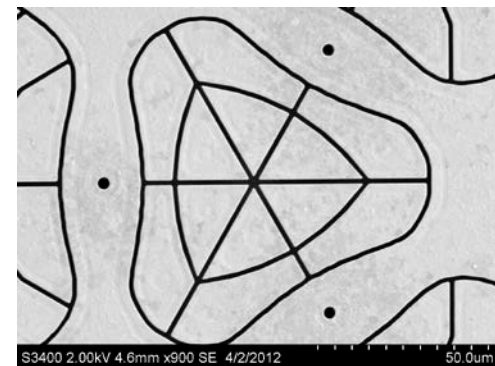
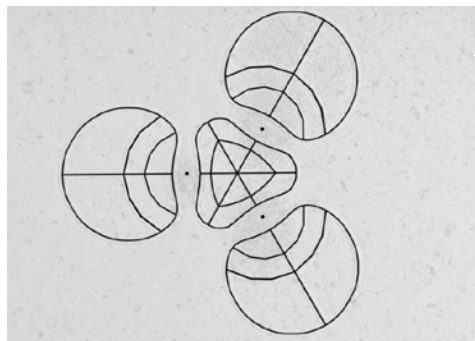
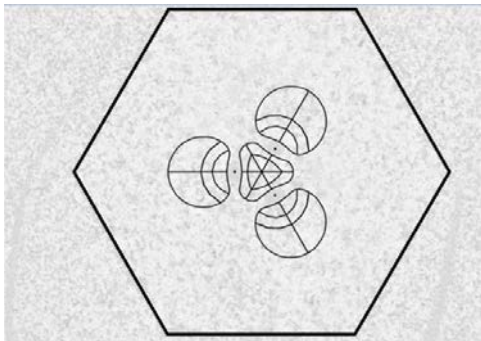


Triangle Trap Rev. 0 – 80 μm , 40 μm triangles

40 μm triangles



80 μm triangles

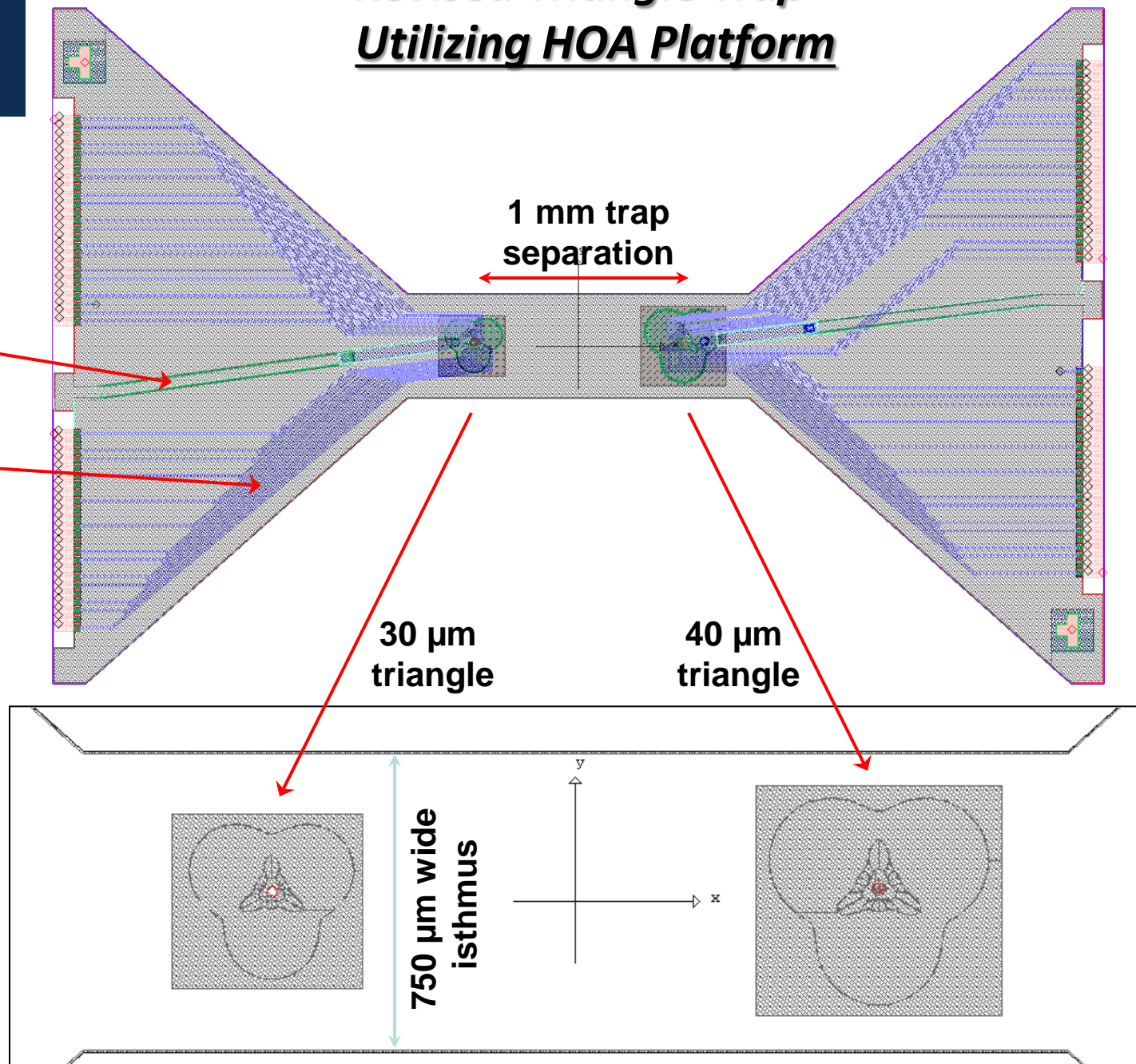




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Revised Triangle Trap Utilizing HOA Platform

- Independent RF leads
- Independent DC controls

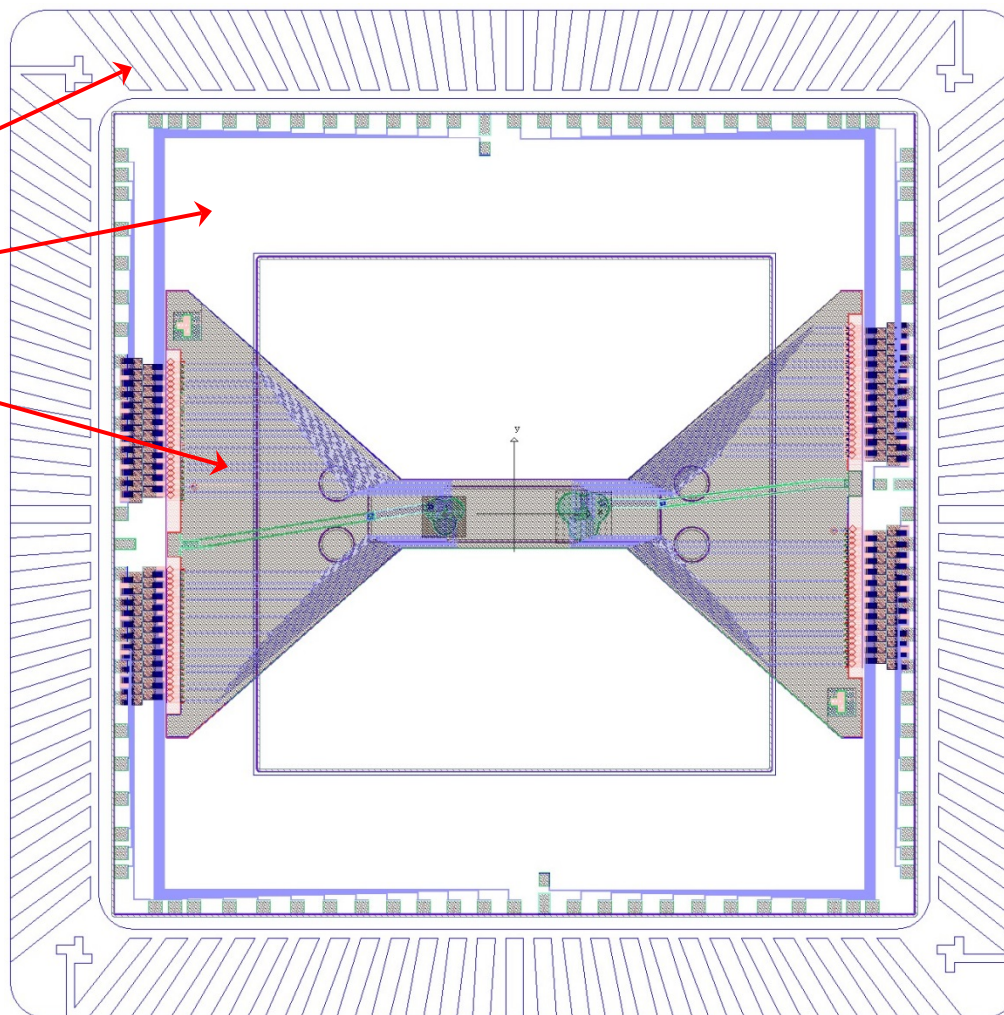




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Revised Triangle Trap **Packaging Design**

- **Package**
- **Interposer**
- **Trap Chip**



Trap Status

Triangle Trap

- Utilize existing 40 μm triangle design
- Add scaled 30 μm triangle design
- Layout complete August 2013
- Photomasks ordered, lot start September 2013
- Device fabrication/packaging completed March 2014

Hex + 1 Trap

- Simulate/design Hex + 1 4LM surface electrode trap utilizing concepts of hexagonal Kitaev trap array (Didi to discuss)
- Perform device layout for Hex + 1 ion trap
 - Independent control for 4 ions in Y configuration



I A R P A

Surface Electrode Ion Trap Technology Overview



Matthew Blain – Org. 1725

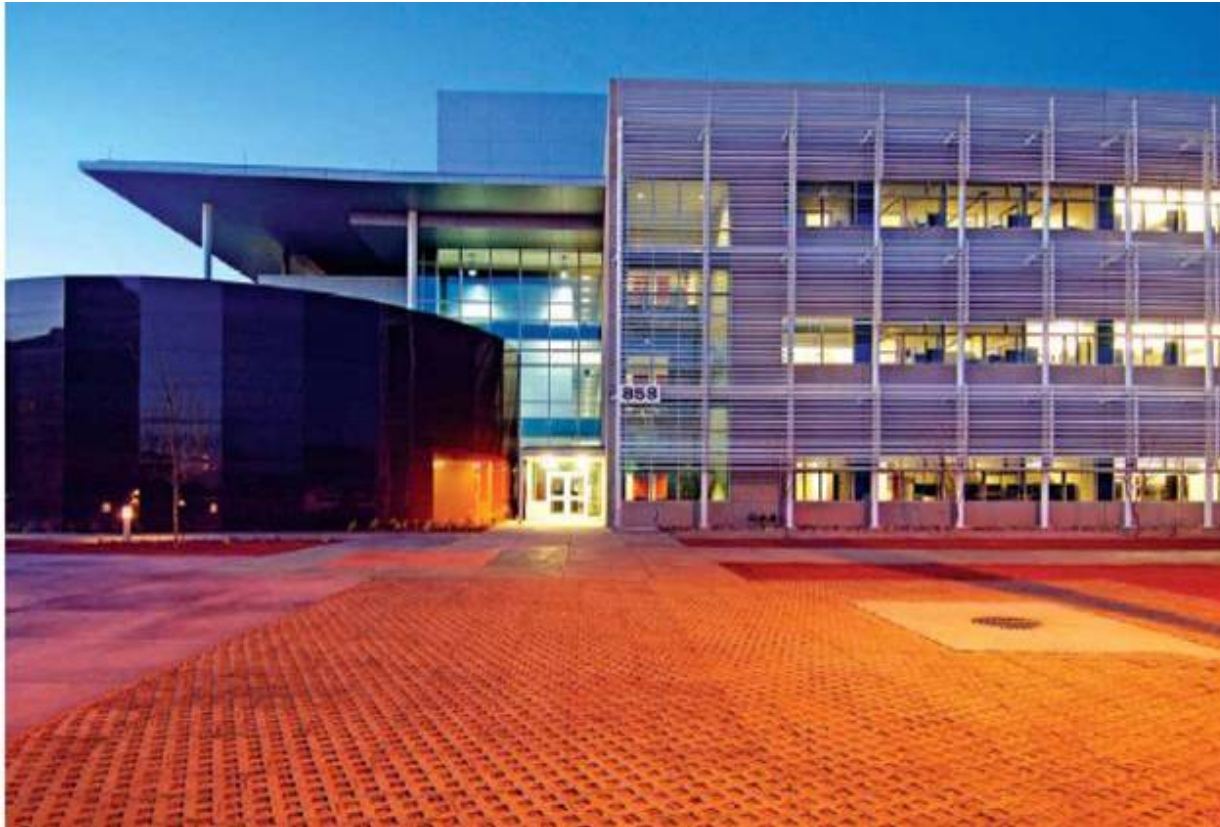


Laboratory Directed
Research & Development

6 August 2013

Experimental

D. Stick
P. Maunz
K. Fortier
D. Sterk
C. Tigges
B. Tabakov
F. Benito
T. Barrick
C. Johnson



Ion Traps

M. Blain
B. Loviza
A. Ortega
E. Heller
R. Haltli
D. Hollowell
L. Fang
J. Gallegos

Micro-Optics

S. Kemme
R. Ellis
R. Boye
A. Young
S. Samora

MESA Staff:

→ SiFab/μFab



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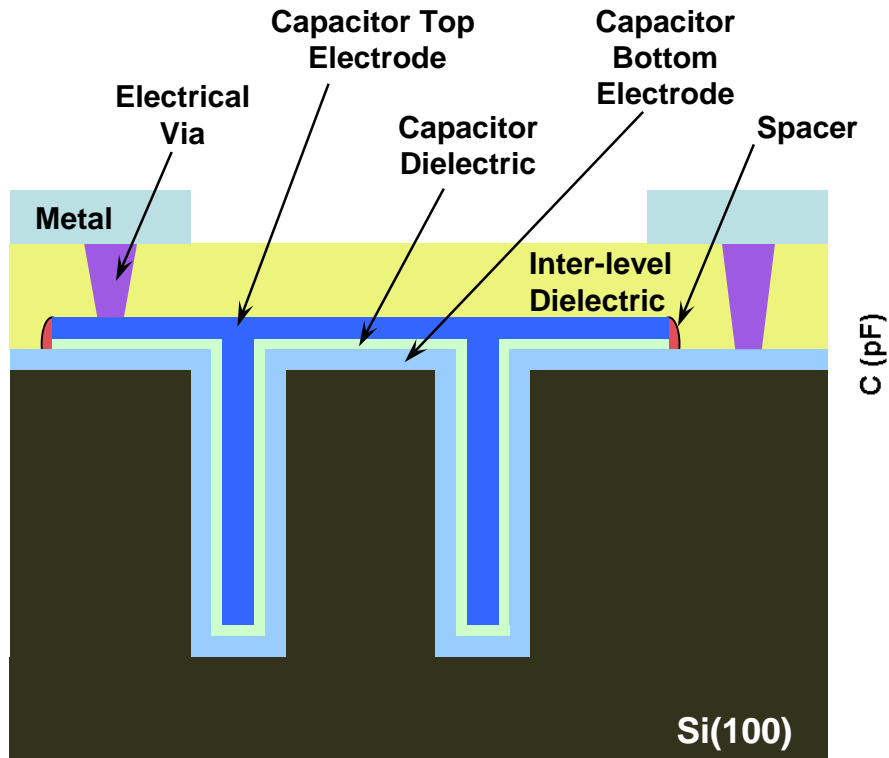


Integrated Trench Capacitors

Trench v. Surface Capacitors for Surface Ion Traps

- High-k dielectric surface areas: still large
- Thin dielectric challenges: yield, reliability
- Vertical surfaces: more available area

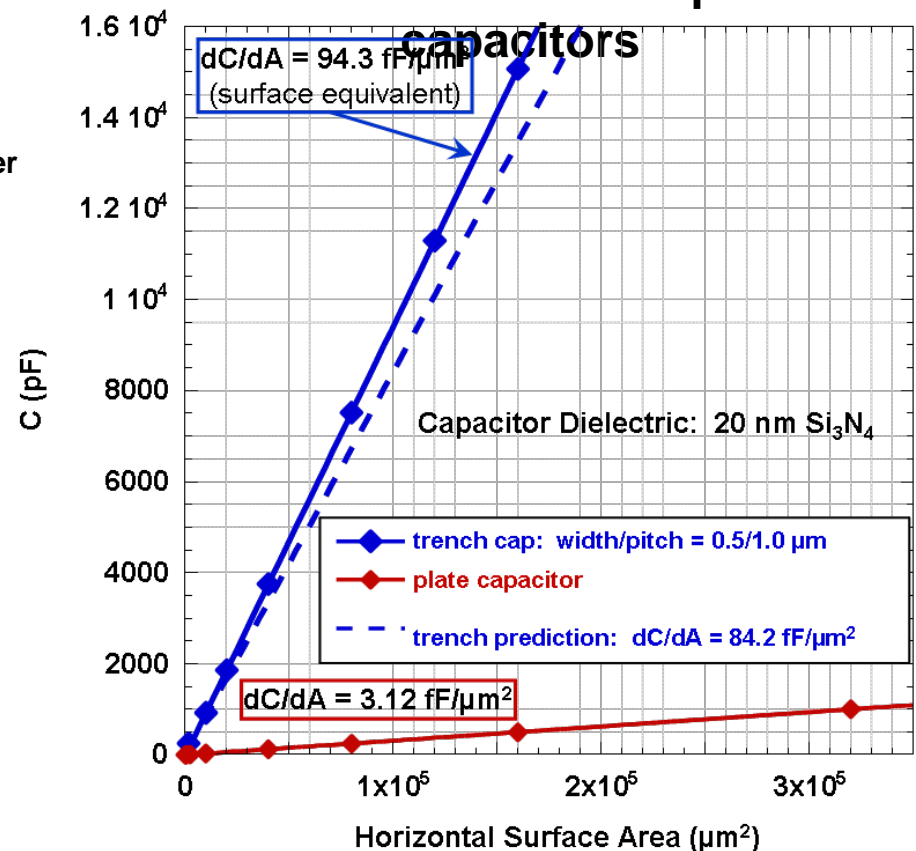
Trench Capacitor Architecture



ATC 116 Series Microcaps

Surface mount: 1.27 x 1.27 mm², 821±20% pF

Area relationship for trench v. horizontal plate

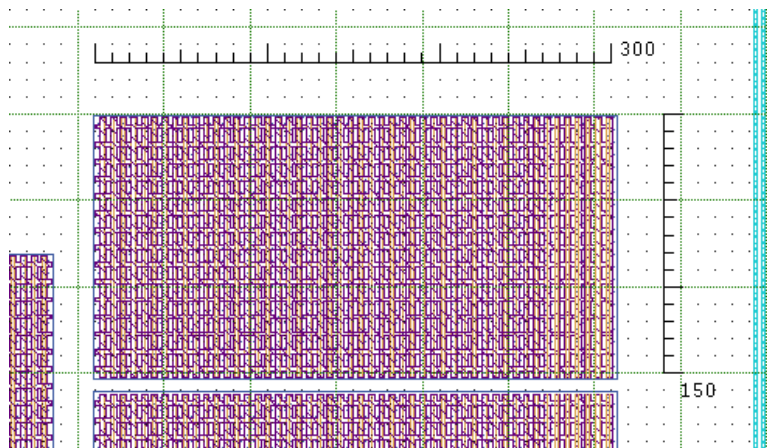




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Integrated Trench Capacitors

1.05 nF trench cap, 0.045 mm²/cap

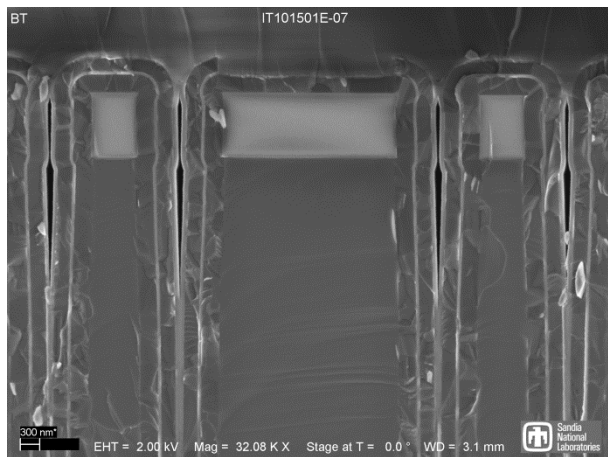
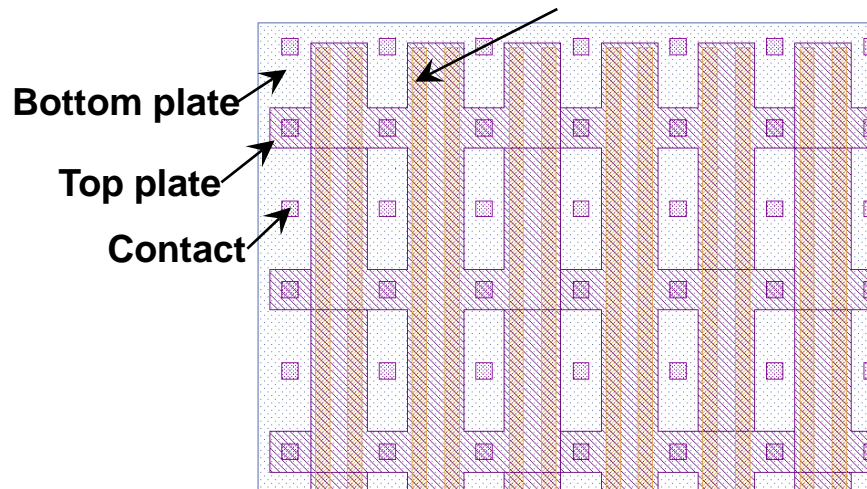


Top plate: 250 nm n-type a-Si

Dielectric: 40 nm Si₃N₄

Bottom plate: 300 nm n-type a-Si

Trenches: 1 μ m wide, 150 μ m long, 19 μ m deep



19 μ m

